

ABSTRACT

A semiconductor memory device includes a substrate including a cell region and a border region, and first to eighth word lines disposed in the substrate to cross the cell region and extending to the border region in a first direction. The first to eighth word lines are sequentially disposed in a second direction, and the first to eighth word lines are sequentially disposed in the order of the first word line, followed by the second word line, followed by the third word line, followed by the fourth word line, followed by the fifth word line, followed by the sixth word line, followed by the seventh word line, and followed by the eighth word line. On the border region, the fourth and eighth word lines extend in the first direction a greater distance than the first to third word lines and the fifth to seventh word lines.

FIG. 2A